Power MOSFET 200 mA, 50 V

N-Channel SOT-23

Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low Threshold Voltage (V_{GS(th)}: 0.85 V-1.5 V) Makes it Ideal for Low Voltage Applications
- Miniature SOT-23 Surface Mount Package Saves Board Space
- BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	50	Vdc
Gate-to-Source Voltage - Continuous	V _{GS}	± 20	Vdc
Drain Current - Continuous @ $T_A = 25^{\circ}C$ - Pulsed Drain Current $(t_p \le 10 \ \mu s)$	I _D I _{DM}	200 800	mA
Total Power Dissipation @ T _A = 25°C	P_{D}	225	mW
Operating and Storage Temperature Range	T _J , T _{stg}	– 55 to 150	ç
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	TL	260	°C

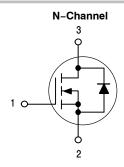
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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200 mA, 50 V $R_{DS(on)} = 3.5 \Omega$





SOT-23 CASE 318 STYLE 21

J1

М



MARKING

Device CodeDate Code*Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BSS138LT1G, BVSS138LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BSS138LT7G	SOT-23 (Pb-Free)	3,500 / Tape & Reel
BSS138LT3G, BVSS138LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

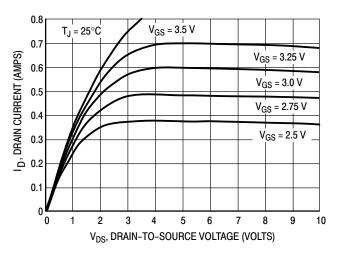
Characteristic			Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 250 μAdc)			50	-	-	Vdc
Zero Gate Voltage Drain Current $ (V_{DS} = 25 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 25^{\circ}\text{C}) $ $ (V_{DS} = 50 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 25^{\circ}\text{C}) $ $ (V_{DS} = 50 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, 150^{\circ}\text{C}) $			- - -	- - -	0.1 0.5 5.0	μAdc
Gate-Source Leakage Current (V _G	I _{GSS}	-	-	±0.1	μAdc	
ON CHARACTERISTICS (Note 1)						
Gate-Source Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$	V _{GS(th)}	0.85	_	1.5	Vdc	
Static Drain-to-Source On-Resistance $ \begin{array}{l} \text{(V}_{GS}=2.75 \text{ Vdc, I}_D<200 \text{ mAdc, T}_A=-40^{\circ}\text{C to }+85^{\circ}\text{C)} \\ \text{(V}_{GS}=5.0 \text{ Vdc, I}_D=200 \text{ mAdc)} \end{array} $		r _{DS(on)}	_ _	5.6 -	10 3.5	Ω
Forward Transconductance (V _{DS} = 25 Vdc, I _D = 200 mAdc, f	9fs	100	-	-	mmhos	
DYNAMIC CHARACTERISTICS				_	_	
Input Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0, f = 1 MHz)	C _{iss}	-	40	50	pF
Output Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0, f = 1 MHz)	C _{oss}	-	12	25	
Transfer Capacitance	(V _{DG} = 25 Vdc, V _{GS} = 0, f = 1 MHz)	C _{rss}	_	3.5	5.0	-
SWITCHING CHARACTERISTICS (Note 2)					
Turn-On Delay Time	t _{d(on)}	-	_	20	ns	
Turn-Off Delay Time	t _{d(off)}	_	-	20		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.

2. Switching characteristics are independent of operating junction temperature.

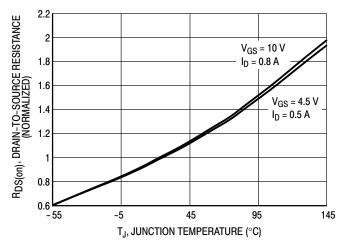
TYPICAL ELECTRICAL CHARACTERISTICS



0.9 25°C $V_{DS} = 10 V$ 0.8 -55°C ID, DRAIN CURRENT (AMPS) 0.7 150°C 0.6 0.5 0.4 0.3 0.2 0.1 0.5 4.5 VGS, GATE-TO-SOURCE VOLTAGE (VOLTS)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



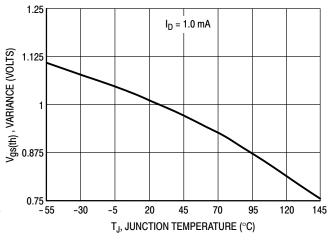
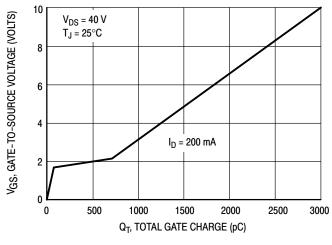


Figure 3. On–Resistance Variation with Temperature

Figure 4. Threshold Voltage Variation with Temperature



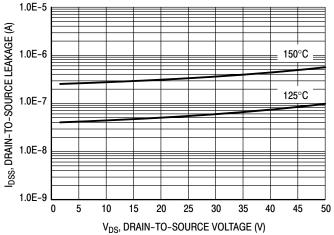
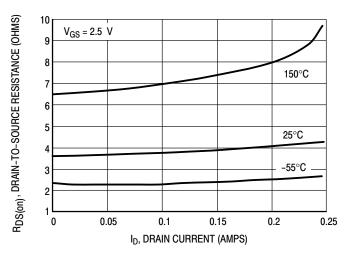


Figure 5. Gate Charge

Figure 6. IDSS

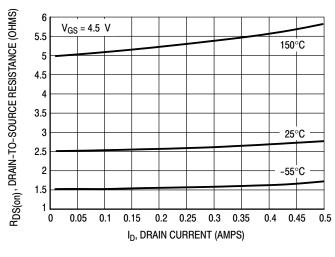
TYPICAL ELECTRICAL CHARACTERISTICS



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Figure 7. On-Resistance versus Drain Current

Figure 8. On-Resistance versus Drain Current



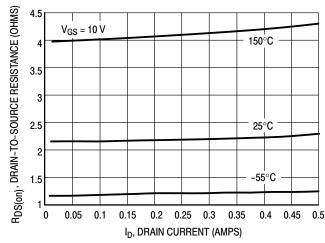
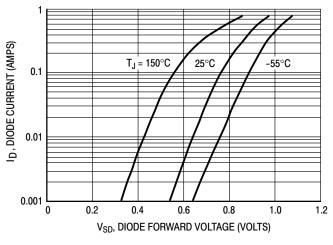


Figure 9. On-Resistance versus Drain Current

Figure 10. On-Resistance versus Drain Current



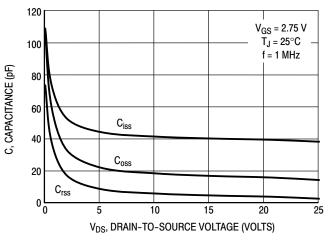


Figure 11. Body Diode Forward Voltage

Figure 12. Capacitance

TYPICAL ELECTRICAL CHARACTERISTICS

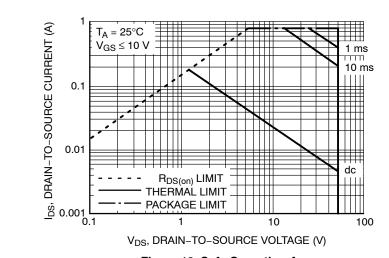


Figure 13. Safe Operating Area





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DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	IETERS		INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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